

## Transient Voltage Suppressors for ESD Protection

# SESDL5V0WB

### DESCRIPTION

The ÂJESDŠ5V0Y ÓÁis designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

#### FEATURES

- Stand-off Voltage: 5.0 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) Per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection
- This is a Pb-Free Device
- Pb-Free package is available
  RoHS product for packing code suffix "G"
  Halogen free product for packing code suffix "H"

## Maximum Ratings @Ta=25℃

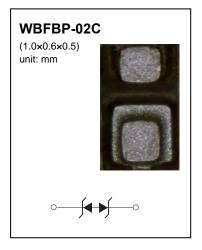
Paramete	Symbol	Limit	Unit				
IEC61000-4-2(ESD)	Air		±30	КV			
	Contact		±30	rv			
ESD Voltage	Per Human Body Model		16	KV			
	Per Machine Model		400	V			
Total Power Dissipation on FR-5 Boa	PD	100	mW				
Thermal Resistance Junction-to-Am	$R_{\Theta JA}$	1250	°C/W				
Lead Solder Temperature - Maximur	ΤL	260	°C				
Junction and Storage Temperature R	T <sub>j,</sub> T <sub>stg</sub>	-55 ~ +150	°C				

Stresses exceeding maximum ratings may damage the device. Maximum Ratings are stress ratings only.

Functional operation above the recommended. Operating conditions is not implied. Extended exposure to

stresses above the recommended operating conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.



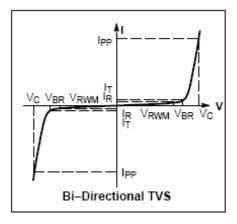


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### **ELECTRICAL CHARACTERISTICS** (Ta = 25°C unless otherwise noted)

Symbol	Parameter					
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current					
Vc	Clamping Voltage @ IPP					
V <sub>RWM</sub>	Working Peak Reverse Voltage					
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>					
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>					
Ι <sub>Τ</sub>	Test Current					
С	Max. Capacitance $@V_R=0$ and f =1MHz					



### ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

Device	Device Marking -	V <sub>RWM</sub> (V)	I <sub>R</sub> (µА) @V <sub>RWM</sub>	<b>V</b> <sub>вR</sub> <b>(V)</b> (Note		Ι <sub>τ</sub>	Vc @IPP = 5 A	I <sub>PP</sub> (A)	V <sub>с</sub> (V) @Max I <sub>PP</sub>	C (pF)
		Max	Max	Min	Max	mA	v	Max	Мах	Мах
SESDL5V0WB	EB	5.0	1.0	5.8	8.8	1.0	10	11.2	12.5	30

2.  $V_{BR}$  is measured with a pulse test current  $I_{T}$  at an ambient temperature of 25°C.